

WHAT IS CLAIMED IS:

1. A method for manufacturing a gate structure of a memory comprises steps of:
providing a substrate;
forming a plurality of gates on the surface of said substrate, each gate having a metal layer;
forming a photoresist layer of a predetermined pattern on the surface of said substrate and on said gates to selectively form an opening between two of said gates;
removing a portion of said metal layer adjacent to said opening; and
removing said photoresist layer.
2. The method as claimed in Claim 1, wherein the substrate comprises silicon.
3. The method as claimed in Claim 1, wherein the metal layer comprises WSi.
4. The method as claimed in Claim 1, wherein the gate further has a poly-silicon formed under the metal layer.
5. The method as claimed in Claim 1, wherein the gate further has a protecting layer formed on the metal layer.
6. The method as claimed in Claim 5, wherein the protecting layer comprises silicon nitride.
7. The method as claimed in Claim 1, wherein the step of removing the portion of the metal layer is performed by wet etching.
8. The method as claimed in Claim 1, wherein the step of removing the portion of the metal layer removes a portion less than 20% of the metal layer.
9. The method as claimed in Claim 1, further comprising a step of forming an insulating layer on the sidewalls of said gate after removing the photoresist layer.
10. The method as claimed in Claim 9, wherein the insulating layer comprises silicon nitride.